Dong-Sing Wuu

List of Publications by Year
in descending order

259 papers	4,524 citations	126907 33 h-index	168389 53 g-index
260 all docs	260 docs citations	260 times ranked	4174 citing authors

#	Article	IF	Citations
1	Tri-layer antireflection coatings (SiO2/SiO2â€“TiO2/TiO2) for silicon solar cells using a solâ€“gel technique. Solar Energy Materials and Solar Cells, 2006, 90, 2710-2719.	6.2	260
2	Low-resistance and high-transparency Ni/indium tin oxide ohmic contacts to p-type GaN. Applied Physics Letters, 2001, 79, 2925-2927.	3.3	172
3	Pulsed laser deposition of gallium oxide films for high performance solar-blind photodetectors. Optical Materials Express, 2015, 5, 1240.	3.0	155
4	High-quality InGaNâˆ•GaN heterojunctions and their photovoltaic effects. Applied Physics Letters, 2008, 93, .	3.3	110
5	Growth and etching characteristics of gallium oxide thin films by pulsed laser deposition. Materials Chemistry and Physics, 2012, 133, 700-705.	4.0	100
6	Improvements of Permeation Barrier Coatings Using Encapsulated Parylene Interlayers for Flexible Electronic Applications. Plasma Processes and Polymers, 2007, 4, 180-185.	3.0	91
7	Properties of SiO2-like barrier layers on polyethersulfone substrates by low-temperature plasma-enhanced chemical vapor deposition. Thin Solid Films, 2004, 468, 105-108.	1.8	84
8	Thermal annealing effect on material characterizations of Î²-Ga2O3 epilayer grown by metal organic chemical vapor deposition. Applied Physics Letters, 2013, 102, .	3.3	67
9	Tunability of p- and n-channel TiOx thin film transistors. Scientific Reports, 2018, 8, 9255.	3.3	61
10	Efficiency improvement of near-ultraviolet InGaN LEDs using patterned sapphire substrates. IEEE Journal of Quantum Electronics, 2005, 41, 1403-1409.	1.9	60
11	Improvement of thermal management of high-power GaN-based light-emitting diodes. Microelectronics Reliability, 2012, 52, 861-865.	1.7	59
12	Surface/structural characteristics and band alignments of thin Ga2O3 films grown on sapphire by pulse laser deposition. Applied Surface Science, 2019, 479, 1246-1253.	6.1	58
13	Water and oxygen permeation of silicon nitride films prepared by plasma-enhanced chemical vapor deposition. Surface and Coatings Technology, 2005, 198, 114-117.	4.8	56
14	Plasma-deposited silicon oxide barrier films on polyethersulfone substrates: temperature and thickness effects. Surface and Coatings Technology, 2005, 197, 253-259.	4.8	55
15	Effects of plasma pretreatment on silicon nitride barrier films on polycarbonate substrates. Thin Solid Films, 2006, 514, 188-192.	1.8	55
16	Investigation of efficiency droop for InGaN-based UV light-emitting diodes with InAlGaN barrier. Applied Physics Letters, 2011, 98, 211107.	3.3	55
17	Defect reduction of laterally regrown GaN on GaN/patterned sapphire substrates. Journal of Crystal Growth, 2009, 311, 3063-3066.	1.5	53
18	Deposition and permeation properties of SiNX/parylene multilayers on polymeric substrates. Surface and Coatings Technology, 2006, 200, 5843-5848.	4.8	52

#	Article	IF	Citations
19	Optimized Thermal Management From a Chip to a Heat Sink for High-Power GaN-Based Light-Emitting Diodes. IEEE Transactions on Electron Devices, 2010, 57, 2203-2207.	3.0	52
20	Fabrication and Study on Red Light Micro-LED Displays. IEEE Journal of the Electron Devices Society, 2018, 6, 1064-1069.	2.1	50
21	Surface Treatments on the Characteristics of Metalâ€“Oxide Semiconductor Capacitors. Crystals, 2019, 9, 1.	2.2	50
22	GaN/Mirror/Si Light-Emitting Diodes for Vertical Current Injection by Laser Lift-Off and Wafer Bonding Techniques. Japanese Journal of Applied Physics, 2004, 43, 5239-5242.	1.5	48
23	Comparison of Erosion Behavior and Particle Contamination in Mass-Production CF4/O2 Plasma Chambers Using Y2O3 and YF3 Protective Coatings. Nanomaterials, 2017, 7, 183.	4.1	47
24	Improved Responsivity Drop From 250 to 200 nm in Sputtered Gallium Oxide Photodetectors by Incorporating Trace Aluminum. IEEE Electron Device Letters, 2018, 39, 220-223.	3.9	46
25	Improved Light Extraction of Nitride-Based Flip-Chip Light-Emitting Diodes Via Sapphire Shaping and Texturing. IEEE Photonics Technology Letters, 2006, 18, 2623-2625.	2.5	45
26	Transparent Barrier Coatings for Flexible Organic Light-Emitting Diode Applications. Chemical Vapor Deposition, 2006, 12, 220-224.	1.3	43
27	85% internal quantum efficiency of 280-nm AlGaN multiple quantum wells by defect engineering. Scientific Reports, 2017, 7, 14422.	3.3	43
28	Study on the effect of size on InGaN red micro-LEDs. Scientific Reports, 2022, 12, 1324.	3.3	41
29	Zinc Gallium Oxideâ€”A Review from Synthesis to Applications. Nanomaterials, 2020, 10, 2208.	4.1	40
30	Effect of resonant cavity in wafer-bonded Green InGaN LED with dielectric and silver mirrors. IEEE Photonics Technology Letters, 2006, 18, 457-459.	2.5	38
31	High performance of Ga-doped ZnO transparent conductive layers using MOCVD for GaN LED applications. Optics Express, 2013, 21, 14452.	3.4	38
32	Efficiency Improvement of GaN-Based LEDs with ITO Texturing Window Layers Using Natural Lithography. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1196-1201.	2.9	37
33	Surface Modification on Wet-Etched Patterned Sapphire Substrates Using Plasma Treatments for Improved GaN Crystal Quality and LED Performance. Journal of the Electrochemical Society, 2011, 158, H988.	2.9	34
34	Thermal Management and Interfacial Properties in High-Power GaN-Based Light-Emitting Diodes Employing Diamond-Added Sn-3Âwt.%Ag-0.5Âwt.%Cu Solder as a Die-Attach Material. Journal of Electronic Materials, 2010, 39, 2618-2626.	2.2	33
35	High-Efficiency 1-mm^{2} AlGaInP LEDs Sandwiched by ITO Omni-Directional Reflector and Current-Spreading Layer. IEEE Photonics Technology Letters, 2007, 19, 492-494.	2.5	32
36	Near-Ultraviolet InGaN/GaN Light-Emitting Diodes Grown on Patterned Sapphire Substrates. Japanese Journal of Applied Physics, 2005, 44, 2512-2515.	1.5	31

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37	Properties of double-layer Al2O3/TiO2 antireflection coatings by liquid phase deposition. Thin Solid Films, 2015, 584, 248-252.	1.8	31
38	Transparent Conductive Oxide Films Embedded with Plasmonic Nanostructure for Light-Emitting Diode Applications. ACS Applied Materials & Interfaces, 2015, 7, 2546-2553.	8.0	31
39	Growth and characterization of co-sputtered aluminum-gallium oxide thin films on sapphire substrates. Journal of Alloys and Compounds, 2018, 765, 894-900.	5.5	31
40	Thinning Technology for Lithium Niobate Wafer by Surface Activated Bonding and Chemical Mechanical Polishing. Japanese Journal of Applied Physics, 2006, 45, 3822-3827.	1.5	30
41	Transparent Barrier Coatings on High Temperature Resisting Polymer Substrates for Flexible Electronic Applications. Journal of the Electrochemical Society, 2010, 157, C47.	2.9	29
42	Co-doped ZnO dilute magnetic semiconductor thin films by pulsed laser deposition: Excellent transmittance, low resistivity and high mobility. Journal of Alloys and Compounds, 2016, 663, 107-115.	5.5	28
43	Surface, structural and optical properties of AlN thin films grown on different face sapphire substrates by metalorganic chemical vapor deposition. Applied Surface Science, 2018, 458, 972-977.	6.1	28
44	Wear and immersion corrosion of Niâ€“P electrodeposit in NaCl solution. Tribology International, 2010, 43, 235-244.	5.9	27
45	Optimization of textured structure on crystalline silicon wafer for heterojunction solar cell. Materials Chemistry and Physics, 2012, 133, 63-68.	4.0	26
46	Simulation and fabrication of heterojunction silicon solar cells from numerical computer and hotâ€wire CVD. Progress in Photovoltaics: Research and Applications, 2009, 17, 489-501.	8.1	25
47	Fabrication of an Ultra-Flexible ZnO Nanogenerator for Harvesting Energy from Respiration. ECS Journal of Solid State Science and Technology, 2013, 2, P400-P404.	1.8	25
48	Pulsed laser deposition of hexagonal GaN-on-Si(100) template for MOCVD applications. Optics Express, 2013, 21, 26468.	3.4	25
49	Preparation and Characterization of Sprayed-Yttrium Oxyfluoride Corrosion Protective Coating for Plasma Process Chambers. Coatings, 2018, 8, 373.	2.6	25
50	Impact of thermal-induced sapphire substrate erosion on material and photodetector characteristics of sputtered Ga2O3 films. Journal of Alloys and Compounds, 2020, 823, 153755.	5.5	25
51	Growth and characterization of InGaN-based light-emitting diodes on patterned sapphire substrates. Journal of Physics and Chemistry of Solids, 2008, 69, 714-718.	4.0	24
52	The role of laser ablated backside contact pattern in efficiency improvement of mono crystalline silicon PERC solar cells. Solar Energy, 2020, 196, 462-467.	6.1	24
53	Surface Texturing for Wafer-Bonded Vertical-Type GaN/Mirror/Si Light-Emitting Diodes. Japanese Journal of Applied Physics, 2005, 44, 3028-3031.	1.5	23
54	Performance of Flip-Chip Thin-Film GaN Light-Emitting Diodes With and Without Patterned Sapphires. IEEE Photonics Technology Letters, 2010, 22, 550-552.	2.5	23

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55	Characteristics of yttrium fluoride and yttrium oxide coatings for plasma process equipment prepared by atmospheric plasma spraying. Japanese Journal of Applied Physics, 2016, 55, 126201.	1.5	23
56	Influences of temperature ramping rate on GaN buffer layers and subsequent GaN overlayers grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2000, 220, 235-242.	1.5	22
57	Direct growth of large grain polycrystalline silicon films on aluminum-induced crystallization seed layer using hot-wire chemical vapor deposition. Thin Solid Films, 2012, 520, 5860-5866.	1.8	22
58	Antireflection and passivation property of titanium oxide thin film on silicon nanowire by liquid phase deposition. Surface and Coatings Technology, 2017, 320, 252-258.	4.8	22
59	Fabrication and characteristics of n-Si/c-Si/p-Si heterojunction solar cells using hot-wire CVD. Thin Solid Films, 2008, 516, 747-750.	1.8	21
60	High-Performance InGaN-Based Green Resonant-Cavity Light-Emitting Diodes for Plastic Optical Fiber Applications. Journal of Lightwave Technology, 2009, 27, 4084-4094.	4.6	21
61	An 83% enhancement in the external quantum efficiency of ultraviolet flip-chip light-emitting diodes with the incorporation of a self-textured oxide mask. IEEE Electron Device Letters, 2013, 34, 274-276.	3.9	21
62	Surface evolution and effect of V/III ratio modulation on etch-pit-density improvement of thin AlN templates on nano-patterned sapphire substrates by metalorganic chemical vapor deposition. Applied Surface Science, 2018, 455, 1123-1130.	6.1	21
63	Efficiency improvement of PERC solar cell using an aluminum oxide passivation layer prepared via spatial atomic layer deposition and post-annealing. Surface and Coatings Technology, 2019, 358, 968-975.	4.8	21
64	Novel Device Design for High-Power InGaN/Sapphire LEDs Using Copper Heat Spreader With Reflector. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1281-1286.	2.9	20
65	Enhanced Output Power of Near-Ultraviolet InGaN/AlGaN LEDs With Patterned Distributed Bragg Reflectors. IEEE Transactions on Electron Devices, 2011, 58, 173-179.	3.0	20
66	Effects of growth temperature and thickness on structure and optical properties of Ga2O3 films grown by pulsed laser deposition. Superlattices and Microstructures, 2019, 131, 21-29.	3.1	20
67	Etching Characteristics and Mechanism of Ba0.7Sr0.3TiO3Thin Films in an Inductively Coupled Plasma. Japanese Journal of Applied Physics, 2000, 39, 2068-2072.	1.5	19
68	Improvement in the Figure of Merit of ITO-Metal-ITO Sandwiched Films on Poly Substrate by High-Power Impulse Magnetron Sputtering. Coatings, 2021, 11, 144.	2.6	19
69	Light extraction enhancement of InGaN light-emitting diode by roughening both undoped micropillar-structure GaN and p-GaN as well as employing an omnidirectional reflector. Applied Physics Letters, 2008, 93, 021125.	3.3	18
70	Improved Conversion Efficiency of Textured InGaN Solar Cells With Interdigitated Imbedded Electrodes. IEEE Electron Device Letters, 2010, 31, 585-587.	3.9	18
71	Permeation barrier coatings by inductively coupled plasma CVD on polycarbonate substrates for flexible electronic applications. Surface and Coatings Technology, 2011, 205, 4267-4273.	4.8	18
72	Influence of oxygen on sputtering of aluminum-gallium oxide films for deep-ultraviolet detector applications. Journal of Alloys and Compounds, 2019, 791, 1213-1219.	5.5	18

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73	Fabrication and Characterization of GaAs Solar Cells on Copper Substrates. IEEE Electron Device Letters, 2009, 30, 940-942.	3.9	17
74	MOCVD Growth of GaN on Sapphire Using a Ga2O3 Interlayer. Journal of the Electrochemical Society, 2011, 158, H1172.	2.9	17
75	Controlling the stress of growing GaN on 150-mm Si (111) in an AlN/GaN strained layer superlattice. Applied Surface Science, 2016, 362, 434-440.	6.1	17
76	Enhanced external quantum efficiencies of AlGaN-based deep-UV LEDs using reflective passivation layer. Optics Express, 2021, 29, 37835.	3.4	17
77	Improvement in Extraction Efficiency of GaN-Based Light-Emitting Diodes with Textured Surface Layer by Natural Lithography. Japanese Journal of Applied Physics, 2005, 44, 2525-2527.	1.5	16
78	Characteristics of Flip-Chip InGaN-Based Light-Emitting Diodes on Patterned Sapphire Substrates. Japanese Journal of Applied Physics, 2006, 45, 3430-3432.	1.5	16
79	Incubation Effects upon Polycrystalline Silicon on Glass Deposited by Hot-Wire CVD. Chemical Vapor Deposition, 2007, 13, 247-252.	1.3	16
80	Effects of RF power and pressure on performance of HF-PECVD silicon thin-film solar cells. Thin Solid Films, 2010, 518, 7233-7235.	1.8	16
81	High indium content InGaN films grown by pulsed laser deposition using a dual-compositing target. Optics Express, 2012, 20, 15149.	3.4	16
82	P-side up AlGaInP-based light emitting diodes with dot-patterned GaAs contact layers. Optics Express, 2013, 21, 19668.	3.4	16
83	Performance of GaN-based light-emitting diodes fabricated using GaN epilayers grown on silicon substrates. Optics Express, 2014, 22, A179.	3.4	16
84	Growth and Characterization of Epitaxial ZnO Nanowall Networks Using Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2008, 47, 746-750.	1.5	15
85	Characterization of MgxZn1â^'xO thin films grown on sapphire substrates by metalorganic chemical vapor deposition. Thin Solid Films, 2011, 519, 1966-1970.	1.8	15
86	Characterization of aluminum gallium oxide films grown by pulsed laser deposition. Ceramics International, 2019, 45, 702-707.	4.8	15
87	Vertical-conducting p-side-up GaN/mirror/Si light-emitting diodes by laser lift-off and wafer-transfer techniques. Physica Status Solidi A, 2004, 201, 2699-2703.	1.7	14
88	Hot-wire chemical vapor deposition and characterization of p-type nanocrystalline SiC films and their use in Si heterojunction solar cells. Thin Solid Films, 2012, 520, 2110-2114.	1.8	14
89	Thin Film GaN LEDs Using a Patterned Oxide Sacrificial Layer by Chemical Lift-Off Process. IEEE Photonics Technology Letters, 2013, 25, 2435-2438.	2.5	14
90	Structural, Surface Morphology and Optical Properties of ZnS Films by Chemical Bath Deposition at Various Zn/S Molar Ratios. Journal of Nanomaterials, 2014, 2014, 1-7.	2.7	14

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91	The Effect of Annealing Ambience on the Material and Photodetector Characteristics of Sputtered ZnGa2O4 Films. Nanomaterials, 2021, 11, 2316.	4.1	14
92	GaN-Based Green Resonant Cavity Light-Emitting Diodes. Japanese Journal of Applied Physics, 2006, 45, 3433-3435.	1.5	13
93	Thermally Stable Mirror Structures for Vertical-Conducting GaN/Mirror/Si Light-Emitting Diodes. IEEE Photonics Technology Letters, 2007, 19, 1913-1915.	2.5	13
94	Hydrogenated amorphous siliconâ€“germanium thin films with a narrow band gap for silicon-based solar cells. Current Applied Physics, 2011, 11, S50-S53.	2.4	13
95	GaN Epilayer Grown on Ga2O3 Sacrificial Layer for Chemical Lift-Off Application. Electrochemical and Solid-State Letters, 2011, 14, H434.	2.2	13
96	Effect of diamond like carbon layer on heat dissipation and optoelectronic performance of vertical-type InGaN light emitting diodes. Applied Physics Letters, 2012, 101, .	3.3	13
97	Improved GaN-on-Si epitaxial quality by incorporating various SixNy interlayer structures. Journal of Crystal Growth, 2014, 399, 27-32.	1.5	13
98	External stress effects on the optical and electrical properties of flexible InGaN-based green light-emitting diodes. Optics Express, 2015, 23, 31334.	3.4	13
99	Transformation from Film to Nanorod via a Sacrifical Layer: Pulsed Laser Deposition of ZnO for Enhancing Photodetector Performance. Scientific Reports, 2017, 7, 14251.	3.3	13
100	On the Role of AlN Insertion Layer in Stress Control of GaN on 150-mm Si (111) Substrate. Crystals, 2017, 7, 134.	2.2	13
101	Quasiâ€Singleâ€Crystalline ZnGa₂O₄ Films via Solid Phase Epitaxy for Enhancing Deepâ€Ultraviolet Photoresponse. Advanced Materials Interfaces, 2019, 6, 1901075.	3.7	13
102	Phosphor-Free White Light From InGaN Blue and Green Light-Emitting Diode Chips Covered With Semiconductor-Conversion AlGaInP Epilayer. IEEE Photonics Technology Letters, 2008, 20, 1139-1141.	2.5	12
103	Investigation of Light Extraction of InGaN LEDs With Surface-Textured Indium Tin Oxide by Holographic and Natural Lithography. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1327-1331.	2.9	12
104	Influence of CH4 flow rate on properties of HF-PECVD a-SiC films and solar cell application. Current Applied Physics, 2011, 11, S21-S24.	2.4	12
105	High thermal stability of high indium content InGaN films grown by pulsed laser deposition. Optics Express, 2012, 20, 21173.	3.4	12
106	Hot-wire chemical vapor deposition and characterization of p-type nanocrystalline Si films for thin film photovoltaic applications. Thin Solid Films, 2012, 520, 5200-5205.	1.8	12
107	Influence of Surface Morphology on the Effective Lifetime and Performance of Silicon Heterojunction Solar Cell. International Journal of Photoenergy, 2015, 2015, 1-8.	2.5	12
108	InGaN LED fabricated on Eco-GaN template with a Ga2O3 sacrificial layer for chemical lift-off application. Vacuum, 2015, 118, 8-12.	3.5	12

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109	Surface passivation property of aluminum oxide thin film on silicon substrate by liquid phase deposition. Thin Solid Films, 2016, 618, 118-123.	1.8	12
110	High power impulse magnetron sputtered p-type Î³-titanium monoxide films: Effects of substrate bias and post-annealing on microstructure characteristics and optoelectrical properties. Materials Science in Semiconductor Processing, 2017, 61, 85-92.	4.0	12
111	Growth and Photocatalytic Properties of Gallium Oxide Films Using Chemical Bath Deposition. Crystals, 2019, 9, 564.	2.2	12
112	Nitrogen and oxygen annealing effects on properties of aluminum-gallium oxide films grown by pulsed laser deposition. Ceramics International, 2020, 46, 24147-24154.	4.8	12
113	Ga2O3 nanorod-based extended-gate field-effect transistors for pH sensing. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2022, 276, 115542.	3.5	12
114	Advanced Atomic Layer Deposition Technologies for Micro-LEDs and VCSELs. Nanoscale Research Letters, 2021, 16, 164.	5.7	12
115	Improvements of N-Side-up GaN Light-Emitting Diodes Performance by Indiumâ€“Tin-Oxide/Al Mirror. Japanese Journal of Applied Physics, 2006, 45, 3449-3452.	1.5	11
116	Enhanced Luminance Efficiency of Wafer-Bonded InGaNâ€“GaN LEDs With Double-Side Textured Surfaces and Omnidirectional Reflectors. IEEE Journal of Quantum Electronics, 2008, 44, 1116-1123.	1.9	11
117	Improved Light Extraction in AlGaInP-Based LEDs Using a Roughened Window Layer. Journal of the Electrochemical Society, 2008, 155, H710.	2.9	11
118	Effect of Crystalline Quality on Photovoltaic Performance for ${m In}_{0.17}{m Ga}_{0.83}{m As}$ Solar Cell Using X-Ray Reciprocal Space Mapping. IEEE Journal of Quantum Electronics, 2011, 47, 1434-1442.	1.9	11
119	Fabrication of Flexible Amorphous-Si Thin-Film Solar Cells on a Parylene Template Using a Direct Separation Process. IEEE Transactions on Electron Devices, 2011, 58, 1433-1439.	3.0	11
120	Lattice deformation of wurtzite Mg Zn1â^'O alloys: An extended X-ray absorption fine structure study. Journal of Alloys and Compounds, 2014, 582, 157-160.	5.5	11
121	Enhanced Deep-Ultraviolet Responsivity in Aluminumâ€“Gallium Oxide Photodetectors via Structure Deformation by High-Oxygen-Pressure Pulsed Laser Deposition. ACS Applied Materials & Interfaces, 2019, 11, 17563-17569.	8.0	11
122	On the mechanism of carrier recombination in downsized blue micro-LEDs. Scientific Reports, 2021, 11, 22788.	3.3	11
123	Growth and characterization of polycrystalline Si films prepared by hot-wire chemical vapor deposition. Thin Solid Films, 2006, 498, 9-13.	1.8	10
124	Improved Performance of 365-nm LEDs by Inserting an Un-Doped Electron-Blocking Layer. IEEE Electron Device Letters, 2014, 35, 467-469.	3.9	10
125	A High-Temperature Die-Bonding Structure Fabricated at Low Temperature for Light-Emitting Diodes. IEEE Electron Device Letters, 2015, 36, 835-837.	3.9	10
126	Optoelectronic Properties and Structural Characterization of GaN Thick Films on Different Substrates through Pulsed Laser Deposition. Applied Sciences (Switzerland), 2017, 7, 87.	2.5	10

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127	Process Integration and Interconnection Design of Passive-Matrix LED Micro-Displays With 256 Pixel-Per-Inch Resolution. IEEE Journal of the Electron Devices Society, 2020, 8, 251-255.	2.1	10
128	High Performance AlGaInP-Based Micro-LED Displays With Novel Pixel Structures. IEEE Photonics Technology Letters, 2021, 33, 1375-1378.	2.5	10
129	Compact Ga2O3 Thin Films Deposited by Plasma Enhanced Atomic Layer Deposition at Low Temperature. Nanomaterials, 2022, 12, 1510.	4.1	10
130	Pulsed laser deposition grown non-stoichiometry transferred ZnGa2O4 films for deep-ultraviolet applications. Applied Surface Science, 2022, 597, 153700.	6.1	10
131	Oxygen annealing induced crystallization and cracking of pulsed laser deposited Ga2O3 films. Vacuum, 2022, 202, 111176.	3.5	10
132	Enhanced Light Output in Roughened GaN-Based Light-Emitting Diodes Using Electrodeless Photoelectrochemical Etching. IEEE Photonics Technology Letters, 2006, 18, 2472-2474.	2.5	9
133	Effects of Transparent Conductive Layers on Characteristics of InGaN-Based Green Resonant-Cavity Light-Emitting Diodes. Japanese Journal of Applied Physics, 2007, 46, 3416-3419.	1.5	9
134	Deposition and characterization of ultra-high barrier coatings for flexible electronic applications. Vacuum, 2010, 84, 1444-1447.	3.5	9
135	Transferring Thin Film GaN LED Epi-Structure to the Cu Substrate by Chemical Lift-Off Technology. Electrochemical and Solid-State Letters, 2011, 14, H281-H284.	2.2	9
136	An Efficient Metal-Core Printed Circuit Board With a Copper-Filled Through (Blind) Hole for Light-Emitting Diodes. IEEE Electron Device Letters, 2013, 34, 105-107.	3.9	9
137	ZnO Nanowires Embedded in Epoxy Resin Separating from the Substrate for Wearable Electronics Applications. IEEE Nanotechnology Magazine, 2014, 13, 458-463.	2.0	9
138	Performance comparison of p-side-up thin-film AlGaInP light emitting diodes with aluminum-doped zinc oxide and indium tin oxide transparent conductive layers. Optical Materials Express, 2016, 6, 1349.	3.0	9
139	Improved Optoelectronic Performance of High-Voltage Ultraviolet Light-Emitting Diodes Through Electrode Designs. IEEE Transactions on Electron Devices, 2017, 64, 4526-4531.	3.0	9
140	Deposition of high-transmittance ITO thin films on polycarbonate substrates for capacitive-touch applications. Vacuum, 2021, 186, 110046.	3.5	9
141	Growth and characterization of co-sputtered Al-doped ZnGa2O4 films for enhancing deep-ultraviolet photoresponse. Applied Surface Science, 2021, 566, 150714.	6.1	9
142	Simultaneous recrystallization, phosphorous diffusion and antireflection coating of silicon films using laser treatment. Thin Solid Films, 2006, 496, 643-648.	1.8	8
143	Hot-wire CVD deposited n-type Î¼c-Si films for Î¼c-Si/c-Si heterojunction solar cell applications. Thin Solid Films, 2008, 516, 765-769.	1.8	8
144	Power-enhanced ITO omni-directional reflective AlGaInP LEDs by two-dimensional wavelike surface texturing. Semiconductor Science and Technology, 2008, 23, 105013.	2.0	8

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145	Repeated Growing and Annealing Towards ZnO Film by Metalâ€Organic CVD. Chemical Vapor Deposition, 2009, 15, 234-241.	1.3	8
146	Study of 375â€‰nm ultraviolet InGaN/AlGaN light-emitting diodes with heavily Si-doped GaN transition layer in growth mode, internal quantum efficiency, and device performance. Journal of Applied Physics, 2011, 110, 123102.	2.5	8
147	Effect of non-vacuum thermal annealing on high indium content InGaN films deposited by pulsed laser deposition. Optics Express, 2013, 21, 7337.	3.4	8
148	Hot-wire chemical vapor deposition of nanocrystalline silicon for ambipolar thin-film transistor applications. Applied Surface Science, 2015, 354, 216-220.	6.1	8
149	Chemical liftâ€off process for nitride LEDs from an Ecoâ€GaN template using an AlN/stripâ€patternedâ€SiO₂ sacrificial layer. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600657.	1.8	8
150	Antireflection and passivation property of aluminium oxide thin film on silicon nanowire by liquid phase deposition. Surface and Coatings Technology, 2018, 350, 1058-1064.	4.8	8
151	Structural and Stress Properties of AlGaN Epilayers Grown on AlN-Nanopatterned Sapphire Templates by Hydride Vapor Phase Epitaxy. Nanomaterials, 2018, 8, 704.	4.1	8
152	Improved Performance of Passive-Matrix Micro-LED Displays Using a Multi-Function Passivation Structure. IEEE Photonics Journal, 2020, 12, 1-11.	2.0	8
153	Structural and photodetector characteristics of Zn and Al incorporated ZnGa2O4 films via co-sputtering. Results in Physics, 2022, 33, 105206.	4.1	8
154	Characterization of Large-Area AlGaInP/Mirror/Si Light-Emitting Diodes Fabricated by Wafer Bonding. Japanese Journal of Applied Physics, 2004, 43, 2510-2514.	1.5	7
155	High-Power AlGaInP Light-Emitting Diodes with Patterned Copper Substrates by Electroplating. Japanese Journal of Applied Physics, 2004, 43, L576-L578.	1.5	7
156	Improvement of indiumâ€“tin oxide films on polyethylene terephthalate substrates using hot-wire surface treatment. Thin Solid Films, 2006, 501, 346-349.	1.8	7
157	An ultrathin (â^¼100Î¼m thick) flexible light plate fabricated using self-alignment and lift-off techniques. Applied Physics Letters, 2007, 91, .	3.3	7
158	Electron-Beam and Sputter-Deposited Indiumâ€“Tin Oxide Omnidirectional Reflectors for High-Power Wafer-Bonded AlGaInP Light-Emitting Diodes. Journal of the Electrochemical Society, 2009, 156, H281.	2.9	7
159	Phase separation phenomenon in MOCVD-grown GaInP epitaxial layers. Journal of Crystal Growth, 2009, 311, 3220-3224.	1.5	7
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